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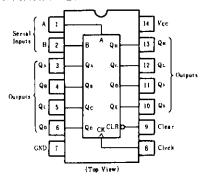
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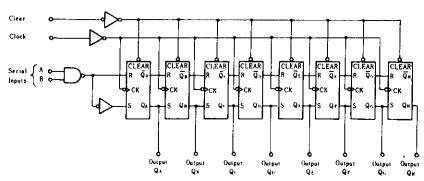
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This 8-bit shift register features gated serial inputs and an asynchronous clear. The gated serial inputs (A and B) permit complete control over incoming data as a low at either (or both) input(s) inhibits entry of the new data and resets the first flip-flop to the low level at the next clock pulse, A high-level input enables the other input which will them determine the state of the first flip-flop. Data at the serial inputs may be changed while the clock is high or low, but only information meeting the setup requirements will be entered. Clocking occurs on the low-to-high-level transition of the clock input.

PIN ARRANGEMENT



BBLOCK DIAGRAM



EFUNCTION TABLE

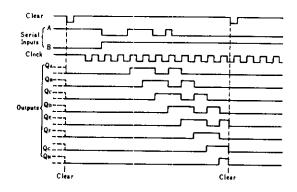
	Inpu	its	Outputs			
Clear	Clock	A	В	Q _A	Q _B ···	··· Q _H
L	×	×	×	L	L	L
Н	L	×	×	QAO	QBO	Qно
Н	1	Н	Н	Н	Q_{An}	QGn
Н	Î	L	×	L	QAn	QGn
Н	Ť	×	L	L	QAn	QGs

■ RECOMMENDED OPERATING CONDITIONS

Item	Symbol	min	typ	max	Unit
Clock frequency	frinck	0	_	25	MHz
Clock pulse width	tic(CK)	20		-	ns
Clear pulse width	Ar(CLR)	20			ns
Data setup time	tau	15	_	_	ns
Data hold time	th.	5	-	_	ns

- Notes) 1. H; high level, L; low level, X; irrelevant
 - 2. †; transition from low to high level
 - Q_{AO}, Q_{BO}, Q_{HO}; the level of Q_A, Q_B, or Q_H, respectively, before the indicated steady-state input conditions were established.
 - QAn. QGn; the level of QA or QG before the most-recent t transition of the clock; indicates a one-bit shift.

TYPICAL CLEAR, SHIFT, AND CLEAR SEQUENCES



ELECTRICAL CHARACTERISTICS ($Ta = -20 \sim +75^{\circ}$ C)

Item	Symbol	Test Conditions	min	typ*	max	Unit	
_	Vin			2.0		****	V
Input voltage	V_{IL}				-	0.8	V
	Von	$V_{CC} = 4.75 \text{V}, V_{IH} = 2 \text{V}, V_{IL} = 0.8 \text{V}, I_{OH} = -400 \mu\text{A}$		2.7	_	i – 1	V
Output voltage			IoL = 4mA	-		0.4	V
	Vor.	$V_{CC} = 4.75 \text{V}, V_{IH} = 2 \text{V}, V_{IL} = 0.8 \text{V}$	$I_{QL} = 8 \text{m A}$	1 _	-	0.5	
	Іін	$V_{CC} = 5.25$ V. $V_I = 2.7$ V	_		20	μΑ	
Input current	IrL	$V_{CC} = 5.25 \text{V}, \ V_I = 0.4 \text{V}$			0.4	mА	
	li .	$V_{CC} = 5.25$ V, $V_I = 7$ V			0.1	m A	
Short-circuit output-current	los	$V_{CC} = 5.25 \text{V}$	20		100	mА	
Supply current**	<i>lee</i>	$V_{CC} = 5.25 \text{V}$		16	27	mА	
Input clamp voltage	VIA	$V_{CC} = 4.75 \text{V}, I_{IN} = -18 \text{mA}$				1.5	V

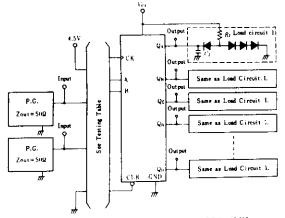
^{*} VCC=5V. Ta=25°C

SWITCHING CHARACTERISTICS ($V_{CC} = 5V$, $T_a = 25^{\circ}C$)

Item	Symbol	Inputs	Outputs	Test Conditions	min	typ	max	Unit
Maximum clock frequency	f _{max}				25	36		MHz
Propagation delay time	ten.	Clear	Q		_	24	36	ns
	tri.#	Clock	Q	$C_L = 15 \text{pF}, R_L = 2 \text{k}\Omega$	-	17	27	ns
	tphi.	Clock	Q	•	-	21	32	ns

TESTING METHOD

1) Test Circuit



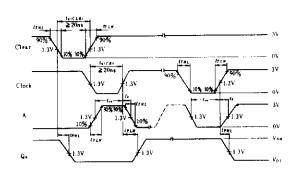
Notes) 1. Input pulse: $t_{TLH} \le 15 \text{ ns}$, $t_{THL} \le 6 \text{ ns}$, PRR = 1 MHz, (Clock, Clear), PRR=500kHz (A or B)

- 2. C_L includes probe and jig capacitance. 3. All diodes are 1S2074 \bigoplus

2) Testing Table

Fre	From input	Inputs			Outputs								
Item	to output	CLR	CK	A	В	QA	Qн	Qc	QD	QE	Qr	Qc	Qн
fmax		4.5V	IN	IN	4.5V	OUT							
telu	Clear→Q	IN	IN	IN	4.5V	OUT							
teni.	CK → Q	4.5V	IN	IN	4.5V	OUT							

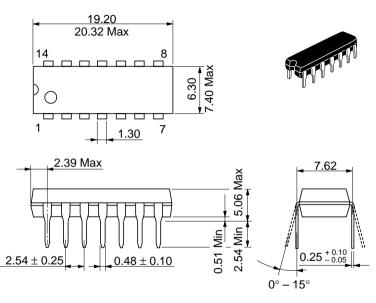
Waveform



Notes) QA output is illustrated. Relationship of serial input A and B data to other Q outputs is illustrated in the timing chart.

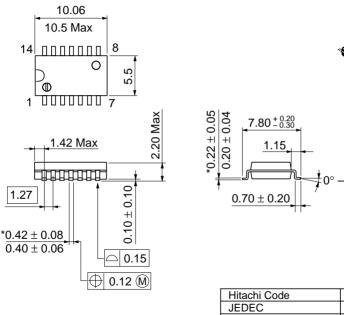
^{**} I_{CC} is measured with outputs open, serial inputs grounded, the clock input at 2.4V, and a momentary grounded, then 4.5V applied to clear.

Unit: mm



Hitachi Code	DP-14
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.97 g

Unit: mm



*Dimension including the plating thickness
Base material dimension

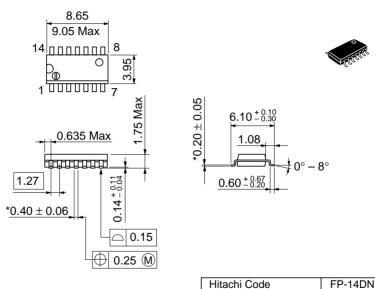
Hitachi Code FP-14DA

JEDEC —

EIAJ Conforms

Weight (reference value) 0.23 g

Unit: mm



JEDEC Conforms EIAJ Conforms Weight (reference value) 0.13 g

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